THE DATASHEET OF

TS8022L

SPDT 50W/125W$_{peak}$ RF Switch 1 MHz to 6.0 GHz

Features

- Frequency Range 1 MHz to 6.0 GHz
- Low insertion loss:
  0.20 dB @ 1.0 GHz
  0.35 dB @ 3.0 GHz
  0.65 dB @ 6.0 GHz
- High isolation:
  42 dB @ 1.0 GHz
  30 dB @ 3.0 GHz
  20 dB @ 6.0 GHz
- 50 W CW Power, 125 W_p Peak Power
- Low power consumption, less than 1 mW
- No external DC blocking capacitors on RF lines
- All RF ports OFF state
- Versatile 2.6...5.25 V power supply
- No need to supply negative voltages

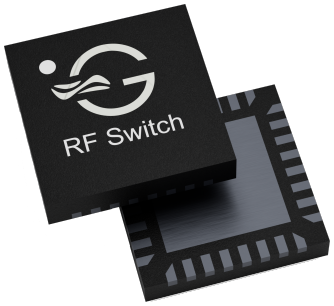


Figure 1: TS8022L in 4.0 x 4.0 mm^2 QFN 32-pin package.

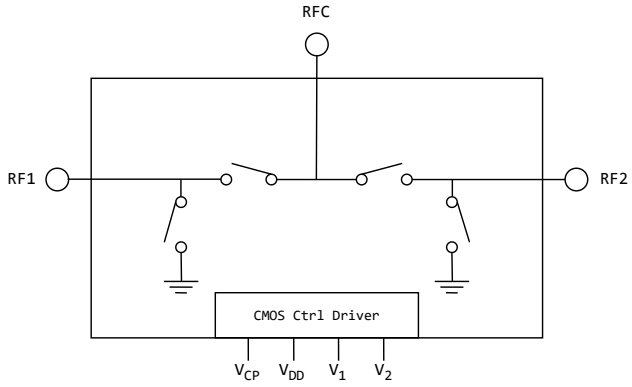


Figure 2: TS8022L functional diagram

Applications

- Private mobile and defense radios
- Public safety handsets
- Cellular infrastructure
- Satellite terminals
- Datalinks

General Description

The TS8022L is a second-generation symmetrical reflective Single Pole Dual Throw (SPDT) switch designed for high-power switching applications. Operating across a 1 MHz to 6.0 GHz bandwidth, the device delivers low insertion loss, high isolation, and excellent linearity in a compact package. With 50 W CW power handling and 125 W peak power capability, the TS8022L is ideally suited for demanding applications requiring superior RF performance.

The TS8022L is housed in a compact 4.0×4.0 mm^2 16-lead Quad Flat No-lead (QFN) plastic package.

RoHS

RoHS10/Reach/Halogen free

Ordering information

Table 1: Ordering Information

Device Part Number	Package Type	Notes
TS8022L	32 Pin 4.0x4.0x0.85 mm^3 QFN	Core part number
TS8022L-EVB	Evaluation Board	
TS8022LMTRPBF[1]	330 mm reel, 3 000pcs	Full reel

[1] MTRPBF - M: Manufacturing, TR: Tape and Reel, and PBF: lead free.

Table 2: Tape and Reel Information

Form	Quantity	Reel Diameter	Reel Width
Tape and Reel	3 000	13” (330mm)	18mm

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Pin Assignment

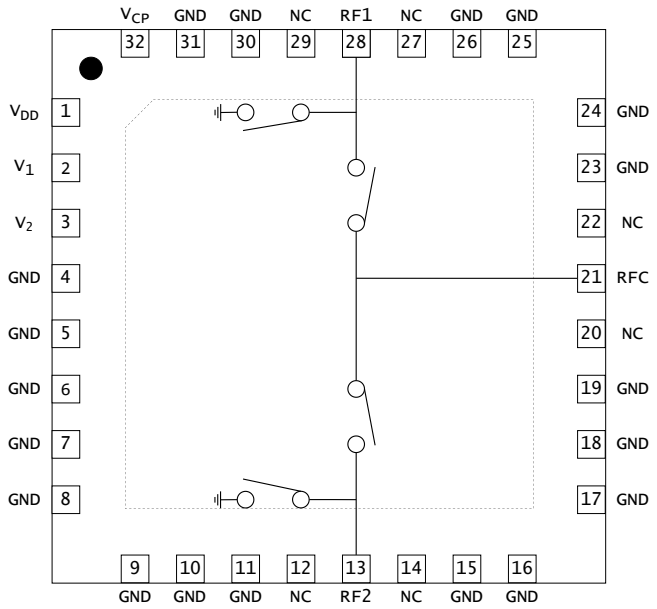


Figure 3: TS8022L pin assignment [top view]

Table 3: Pin Definition

Pin Number	Pin Name	Decription
32	V_{CP}	Internal charge pump voltage output, connect a 1nF capacitor to GND on this node.
1	V_{DD}	DC Power Supply
2	V_1	Switch control input 1
3	V_2	Switch control input 2
13	RF2	RF port 2
21	RFC	RF Common port / Antenna port
28	RF1	RF port 1
12,14,20,22,27,29	NC	NC, Do not connect for adequate clearance and creepage
4,5,6,7,8,9,10,11	GND	Connect to ground[2]
15,16,17,18,19		
23,24,25,26,30,31		
33 [1]	GND	Ground thermal pad, please connect to GND

[1] The backside ground (thermal) pad of the package must be grounded directly to the ground plane of PCB with multiple vias, and adequate heat sinking must be used to ensure proper operation and thermal management.
[2] These pins are NC pins inside the package. To avoid floating pins around RF lines, we request these to be connected to ground.

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Absolute Maximum Ratings

Table 4: Absolute Maximum Ratings $T_A = +25$°C unless otherwise specified[1].

Parameter	Symbol	Value	Unit
Electrical Ratings			
Power Supply Voltage	V_{DD}	5.5	V
Storage Temperature Range	T_{st}	-55...+125	°C
Operating Temperature Range	T_{op}	-40...+85	°C
Maximum Junction Temperature	T_j	+140	°C
Max RF CW input power, $\geq$ 400MHz[3]	RFx/RFC	48	dBm
Max RF CW input power, 10-400MHz[3]	RFx/RFC	47	dBm
Max RF CW input power, $\geq$ 400MHz, 20% duty cycle, 2.0 ms pulse [2,3]	RFx/RFC	50	dBm
Max RF peak input power, $\geq$400MHz, 1% duty cycle, 10 μs pulse [2]	RFx/RFC	52	dBm
Max RF peak voltage 30MHz	RFx/RFC	yy	V
Max RF peak voltage 800MHz	RFx/RFC	yy	V
Thermal Ratings			
Thermal Resistance (junction-to-case) – Bottom side	$R_{\theta jc}$	5.4	°C/W
Soldering Temperature	T_{solder}	+260	°C
ESD Ratings			
Human Body Model (HBM)	Level 1B	500...<1000	V
Charged Device Model (CDM)	Level C3	$\geq$1000	V
Moisture Rating			
Moisture Sensitivity Level[4]	MSL	1	

[1] Maximum ratings are absolute ratings. Exposure to absolute maximum rating conditions for extended periods may affect device reliability and can cause permanent damage to the device. Exceeding one or a combination of the absolute maximum ratings may cause permanent and irreversible damage to the device and/or to surrounding circuit. Functional operation of the device is not implied in any conditions above those indicated in the Electrical Specifications section.
[2] Test frequency 800MHz.
[3] See Power De-rating table for low frequencies.
[4] Tagore recommends to store part in moisture barrier bags to preserve solderability.

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Electrical Specifications

Table 5: Electrical Specifications $T_A = +25°C; V_{DD} = +3.3V; 50\Omega$ Source/Load.

Parameter	Condition	Minimum	Typical	Maximum	Unit
Operating frequency	f	1		6000	MHz
Insertion loss	30 MHz		0.15		dB
unmatched, upto 4.5 GHz	1.0 GHz		0.20	0.30	dB
$RFC - RFx$	3.0 GHz		0.35		dB
	4.5 GHz		0.60		dB
Insertion loss[1]	30 MHz		0.15		dB
matched upto 6.0 GHz	1.0 GHz		0.20		dB
$RFC - RFx$	3.0 GHz		0.50		dB
	5.0 GHz		0.50		dB
	6.0 GHz		0.65		dB
Isolation	30 MHz		60		dB
unmatched, upto 4.5 GHz	1.0 GHz	40	43		dB
$RFC - RFx$	3.0 GHz		28		dB
	4.5 GHz		23		dB
Isolation[1]	30 MHz		60		dB
matched upto 6.0 GHz	1.0 GHz		43		dB
$RFC - RFx$	3.0 GHz		28		dB
	5.0 GHz		22		dB
	6.0 GHz		18		dB
Isolation[1]	30 MHz		55		dB
Isolation state	1.0 GHz		36		dB
$RFC - RFx$	3.0 GHz		26		dB
	5.0 GHz		17		dB
	6.0 GHz		16		dB
Isolation[1]	30 MHz		60		dB
Isolation state	1.0 GHz		55		dB
$RF1 - RF2$	3.0 GHz		48		dB
	5.0 GHz		48		dB
	6.0 GHz		35		dB

[1] Matched values are not guaranteed as they include performance of matching components. These components are beyond control of TagoreTech and therefore given values are indications, not guaranteed values.

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Table 6: Electrical Specifications $T_A = +25°C; V_{DD} = +3.3V; 50\Omega$ Source/Load.

Parameter	Condition	Minimum	Typical	Maximum	Unit
Operating frequency	f	1		6000	MHz
Return Loss	30 MHz		-30		dB
unmatched, upto 4.5 GHz	1.0 GHz		-30	-25	dB
$RFC - RFx$	3.0 GHz		-16		dB
	4.5 GHz		-15		dB
Return Loss[1]	30 MHz		-30		dB
matched upto 6.0 GHz	1.0 GHz		-25		dB
$RFC - RFx$	3.0 GHz		-13		dB
	5.0 GHz		-16		dB
	6.0 GHz		-16		dB

[1] Matched values are not guaranteed as they include performance of matching components. These components are beyond control of TagoreTech and therefore given values are indications, not guaranteed values.

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Table 7: Electrical Specifications $T_A = +25°C; V_{DD} = +3.3V; 50\Omega$ Source/Load.

Parameter	Condition	Minimum	Typical	Maximum	Unit
Operating frequency	f	1		6000	MHz
Harmonic Distortion					
H_2	800MHz, P_{in} =45dBm		-86		dBc
H_3	800MHz, P_{in} =45dBm		-89		dBc
IIP3	800MHz		71		dBm
Power and Compression point					
P_{maxCW}[2]	Max RF CW Power 400-f_{max}		47		dBm
P_{maxCW}[2]	Max RF CW Power 10-400		46		dBm
P_{maxpeak}	Max RF Peak Power 400-f_{max}		51		dBm
$P_{\text{0.1dB}}$	800MHz, CW		47		dBm
$P_{\text{peak0.1dB}}$	800MHz, 1% duty cycle, 10μs pulse		48		dBm
P_{1dB}[1]	800MHz, CW		49		dBm
$P_{\text{maxhot RFx}}$[5]	Max RF CW Power, hot switching		40		dBm
$P_{\text{maxhot RFC}}$[5]	Max RF CW Power, hot switching		40		dBm

[1] $P_{1\,\text{dB}}$ has been given for comparison reasons only. Please do not exceed Absolute Maximum ratings.
[2] See Power De-rating table
[5] Dependent on thermal design and surrounding circuits.

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Table 8: Electrical Specifications $T_A = +25°C; V_{DD} = +3.3V; 50\Omega$ Source/Load.

Parameter	Condition	Minimum	Typical	Maximum	Unit
Operating frequency	f	1		6000	MHz
Noise					
CP switching noise[4]	RBW=1kHz		-140		dBm
Switching Time					
t_{ON}[8]	Switch ON time		5.2	9.0	μs
t_{OFF}[8]	Switch OFF time		5.2	9.0	μs
t_{RISE}[8]	Switch RISE time		4.5	5.0	μs
t_{FALL}[8]	Switch FALL time		4.5	7.0	μs
t_{wON}	Minimum Switch ON time		3.6		μs
t_{wOFF}	Minimum Switch OFF time		3.6		μs
f_{PRR}, $C_{VCP} = 1nF$[3]	Maximum pulse repetition rate		1		kHz
f_{PRR}, $C_{VCP} = 10nF$[3]	Maximum pulse repetition rate		1.4		kHz
f_{PRR}, $C_{VCP} = 100nF$[3]	Maximum pulse repetition rate		1.8		kHz
f_{PRR}, $V_{CPext} = -18\,V$[6]	Maximum pulse repetition rate		>20		kHz
$t_{startup}$, $C_{VCP} = 1nF$[3]	startup time		0.8		ms
$t_{startup}$, $C_{VCP} = 10nF$[3]	startup time		7		ms
$t_{startup}$, $C_{VCP} = 100nF$[3]	startup time		40		ms
Power Supply, DC					
Control voltage[7]	Power Supply V_{DD}	2.6	3.3	5.25	V
	All control pins high, V_{ih}	1.0	3.3	5.25	V
	All control pins low, V_{il}	-0.3	0	0.5	V
Control current	All control pins high, I_{ih}			7.5	μA
	All control pins low, I_{il}		0		μA
Current consumption	I_{DD}, active mode (V_{DD} on)		160	260	μA

[3] With internal charge pump and with C_{VCP}.
[4] Above 250 MHz. For operation at VHF frequencies, below 250 MHz, consider charge pump bypass switch version, if charge pump noise is critical for your application. Please contact TagoreTech for more information.
[5] Dependent on thermal design and surrounding circuits.
[6] External -18 V applied to V_{CP} pin.
[7] Control voltage V_{ih} cannot be higher than V_{DD} (to avoid forward biasing of ESD diode)
[8] Switching time characterization done at 30 Hz and 500 Hz pulse repetition rate (rate to change switch state, for example between RFC-RF1 and RFC-RF2).

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Switching time definition

Example of the definition by using 10 W/40 dBm signal. We apply 10W signal to RF port, stabilized with isolator. Isolator is needed as our switch shows to RF port approximately 4Ω impdance. Lets assume that that switch insertion loss is 0.3 dB. Therefore 90% of the RF signal is 39.55 dBm and 10% of the RF signal is 1W/30dBm. We need to take into account 0.3dB insertion loss, therefore numbers are 39.25 dBm and 29.7 dBm respectively. We change the control from low to high and our time reference point is when our control signal exceeds lower threshold value V_{ihlow}. In certain measurements when control signal rise time is significantly shorter than RF output signal, we approximate start of the clock with 50% point of of control signal.

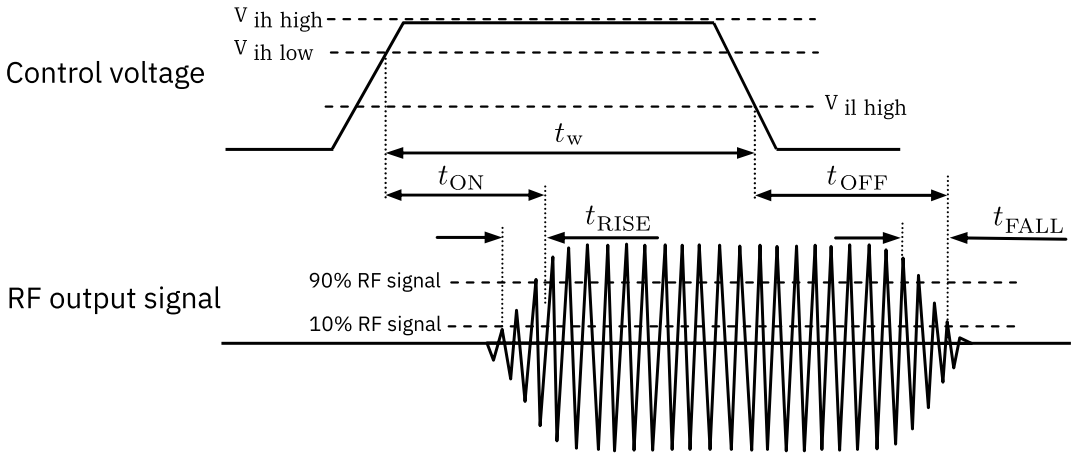


Figure 4: Switching time definition, t_{ON}, t_{OFF}, t_{RISE}, t_{FALL}. Minimum pulse width t_w.

Our component uses integrated charge pump. Maximum pulse repetition rate defines what is maximum frequency for switching events. Please do not exceed given maximum frequency. By feeding external -18 V to V_{CP}, one can improve maximum pulse repetition rate f_{PRR}. Feeding external -18V to V_{CP}, one can drive switch at least to 20kHz f_{PRR}. Expect current consumption of 10mA of -18V.

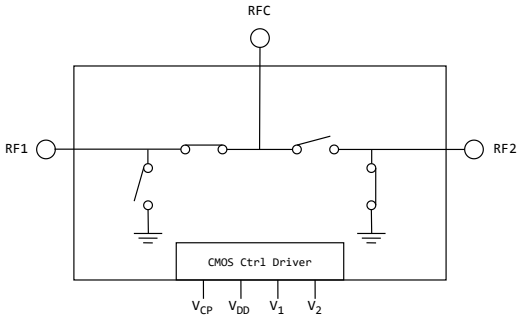
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Switch Control table

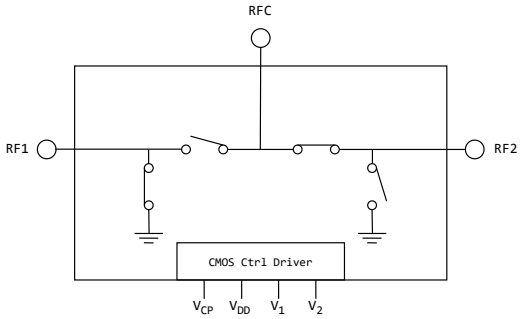
Table 9: Switch Control Table

V_{DD}[1]	V_2	V_1	**Switch state**
1	0	0	RFC – RF1 ON[2]
1	0	1	RFC – RF2 ON
1	1	0	ISO (Isolation), RFC port open, RF ports shorted[3].
0	0	0	V_{DD} off (Isolation), all FETs are on, short shown to RFC and RF ports

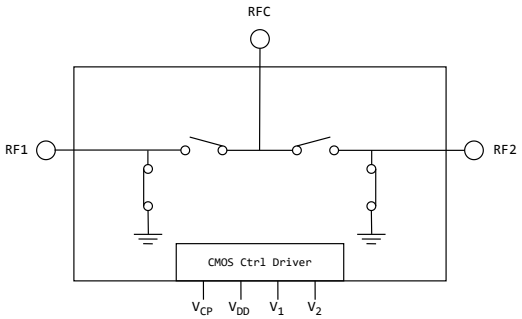
[1] V_{DD} should be applied first before V_1 and V_2, otherwise may cause damage to the device.
[2] There are internal pull-downs to ground on both V_1 and V_2 control pins, the state at start-up without any control voltage applied will be RFC – RF1 ON.
[3] If ISO state is not used, the switch can be operated with single control pin V_1



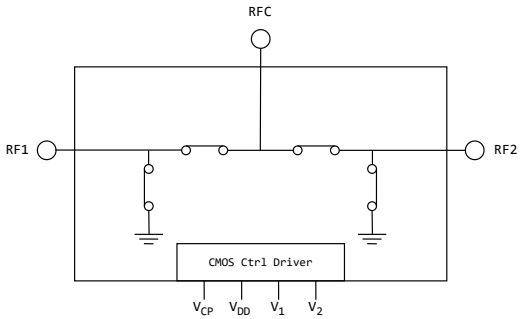
RFC-RF1 ON



RFC-RF2 ON



ISO (Isolation state)



V_{DD} off state

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Theory of Operation

Isolation modes

TS8022L has two isolation modes. Both Isolation mode measurements are shown at electrical performance section. Both modes described below.

Device powered off

When V_{DD} is 0V, all switch RF transistors are on, ie. every MOSFET is on. This means that series MOSFETS and shunt MOSETs are conducting. Every RF port is essentially connected to ground, including ANT port. This is practical when device is directly connected to ANT, there is certain protection against induced electrical fields. This can partially protect radio equipment against electrical fields, when device is not in usage.

Device powered, ISO state

In this state, series MOSFETs are OFF, ie. OPEN and shunt MOSFETs are on, ie. closed. RF1 to RF2 isolation is maximum and antenna is completely isolated. ANT port is open, whereas RFx ports are showing effectively short. Low frequency isolation in this case is approximately 60dB as basically there is DC block due to open FETs.

Feeding external V_{CP} voltage of -18 V

TS8022L supports external voltage supply to V_{CP} to increase pulse repetition rate f_{PRR}. With external voltage supply, f_{PRR} can be increased at least to support pulse repetition rate more than 20 kHz, in some cases even up to 100 kHz. In order to use external voltage, it is mandatory to supply first V_{DD}, have a delay of 1 ms and then apply -18 V to V_{CP}. Shutdown should be in opposite order.

Applications

TS8022L is offering 50 W/125 W_{peak} capability from 1 MHz to 6000 MHz frequency band. Applications include narrowband and multi-octave wideband radios, jammers, EMC testing, public mobile radios, industrial and scientific applications. In the past, such applications were covered with power hungry and complex PIN diodes, TS8022L significantly reduces design complexity for such RF switching needs. TS8022L works well upto 4.0 GHz frequency without external matching components, for frequency above 4.0 GHz, matching is recommended. Datasheet provides an example matching and its performance.

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Schematics and Evaluation Board

S-parameters of the both presented EVBs can be downloaded from link: Download TS8022L S-parameters

Table 10: Port definitions in s-parameter files and plots.

PIN name	Port numbers	S-parameters	Function
RFC	1	S11	
RF1	2	S22	
RF2	3	S33	
RF1ON	12	S21	RFC-RF1 ON
RF2ON	13	S31	RFC-RF2 ON

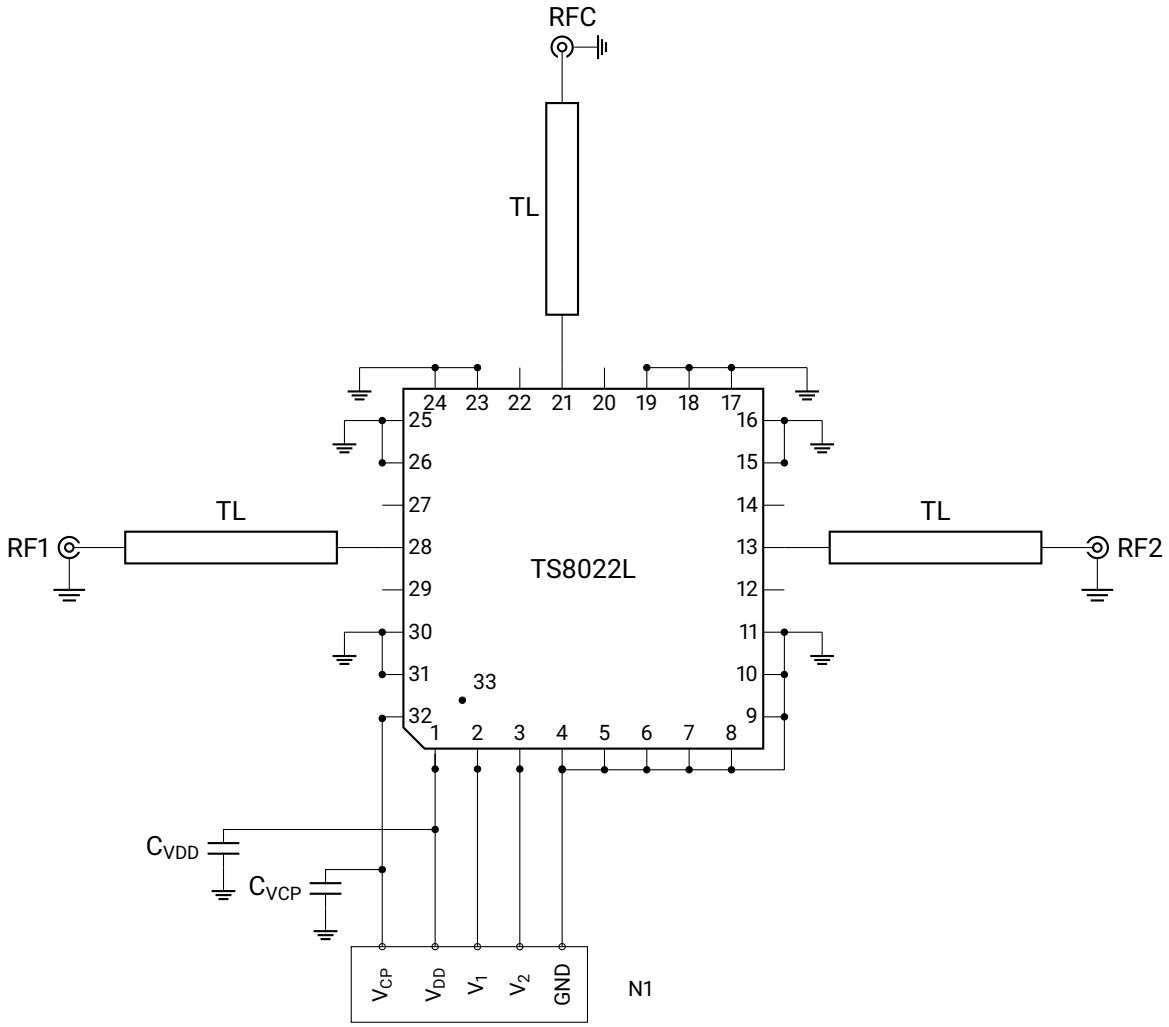
Content of s-parameter repository:

```
TS8022L.zip
├── IDX_00_no_match ..... Directory for s-parameters without matching components
│   ├── Readme.txt
│   ├── TS8022L_RFOFF_3PORT.s3p ..... S3P file for ISO mode
│   ├── TS8022L_VDDOFF_3PORT.s3p ..... S3P file for VDD off mode
│   ├── TS8022L_RF1ON_3PORT.s3p ..... S3P file for RFC-RF1ON mode
│   ├── TS8022L_RF2ON_3PORT.s3p ..... S3P file for RFC-RF2ON mode
│   ├── TS8022L_IDX00_IL_RL.png ..... insertion loss and return loss plot
│   └── TS8022L_IDX00_ISO ..... isolation plot
└── IDX_01_wideband ..... Directory for s-parameters with matching components, 6.0 GHz
    ├── Readme.txt
    ├── TS8022L_RFOFF_3PORT.s3p ..... S3P file for ISO mode
    ├── TS8022L_VDDOFF_3PORT.s3p ..... S3P file for VDD off mode
    ├── TS8022L_RF1ON_3PORT.s3p ..... S3P file for RFC-RF1ON mode
    ├── TS8022L_RF2ON_3PORT.s3p ..... S3P file for RFC-RF2ON mode
    ├── TS8022L_IDX01_IL_RL.png ..... insertion loss and return loss plot
    └── TS8022L_IDX01_ISO.png ..... isolation plot
```


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Performance upto 4.5 GHz, unmatched

TS8022L shows best performance upto 4.5 GHz frequency without any matching components. Only two external components are recommended, 1 nF for V_{CP} and 10nF forV_{DD} lines for supporting charge pump and power supply.



Schematics of TS8022L EVB

Table 11: Components used for TS8022L EVB

Reference	Part number / Value	Description	Notes
C_{VDD}	10nF	Capacitor	GRM155R71H103KA88
C_{VCP}	0.1μF	Capacitor	GRM155R61E104KA87D

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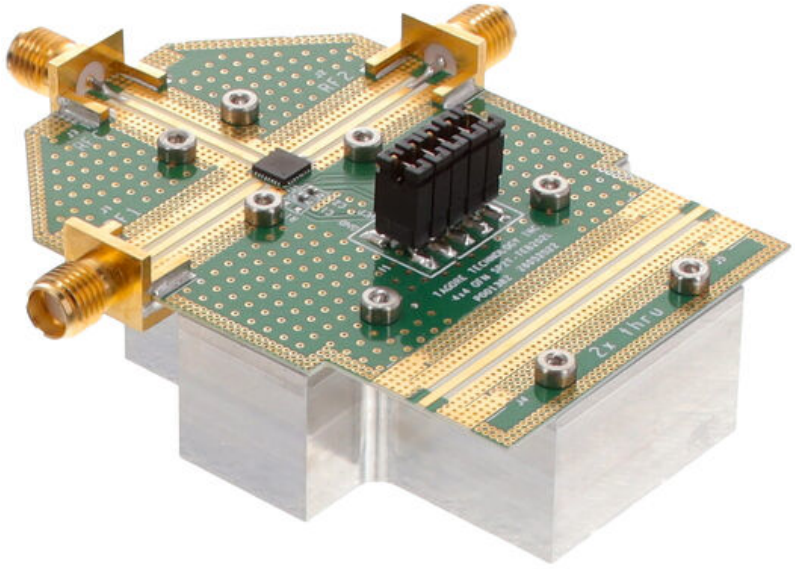
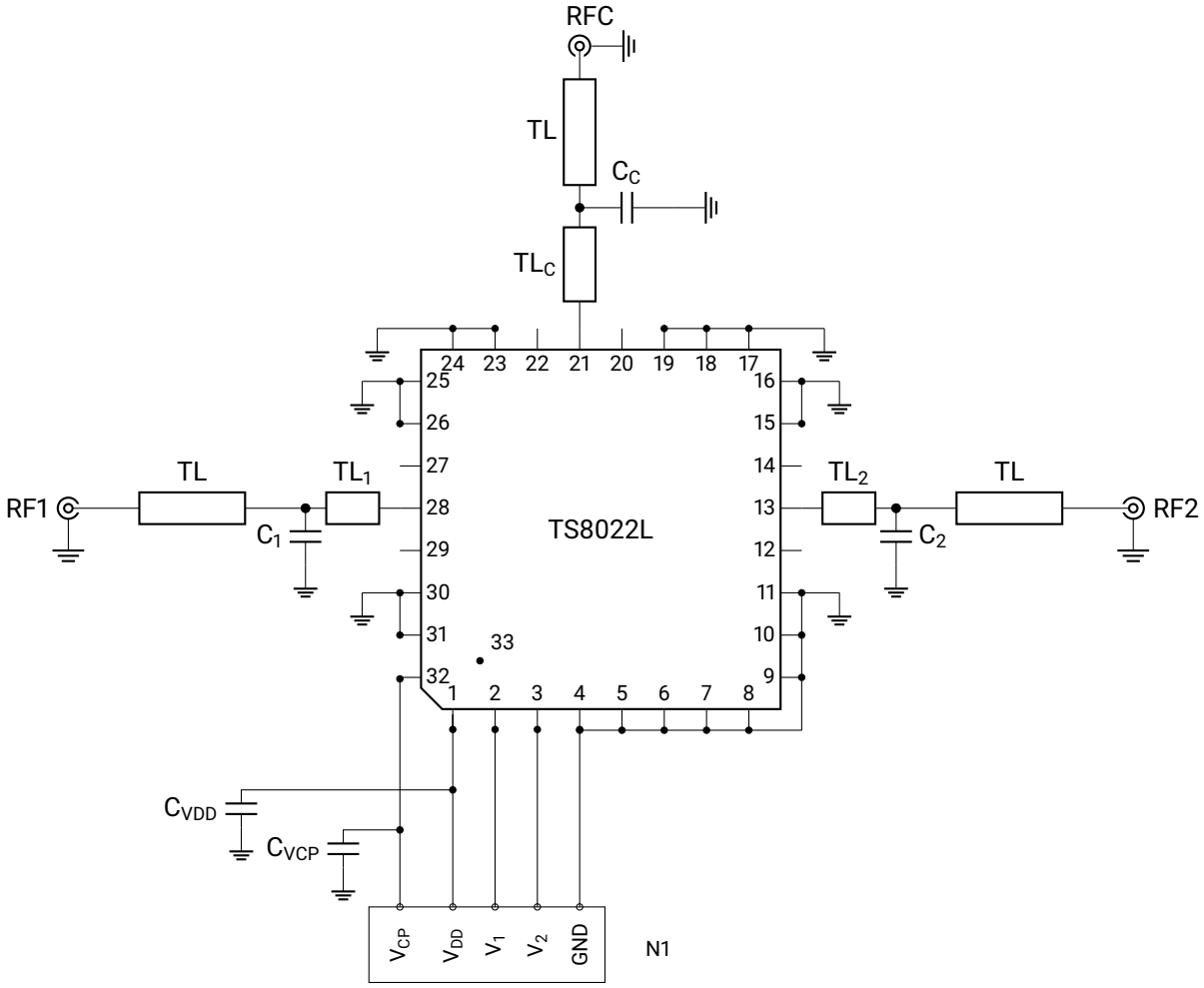


Photo of TS8022L EVB

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Performance upto 6.0,GHz, matched



Schematics of TS8022L EVB with matching components

Table 12: Matching components used for 6.0 GHz performance

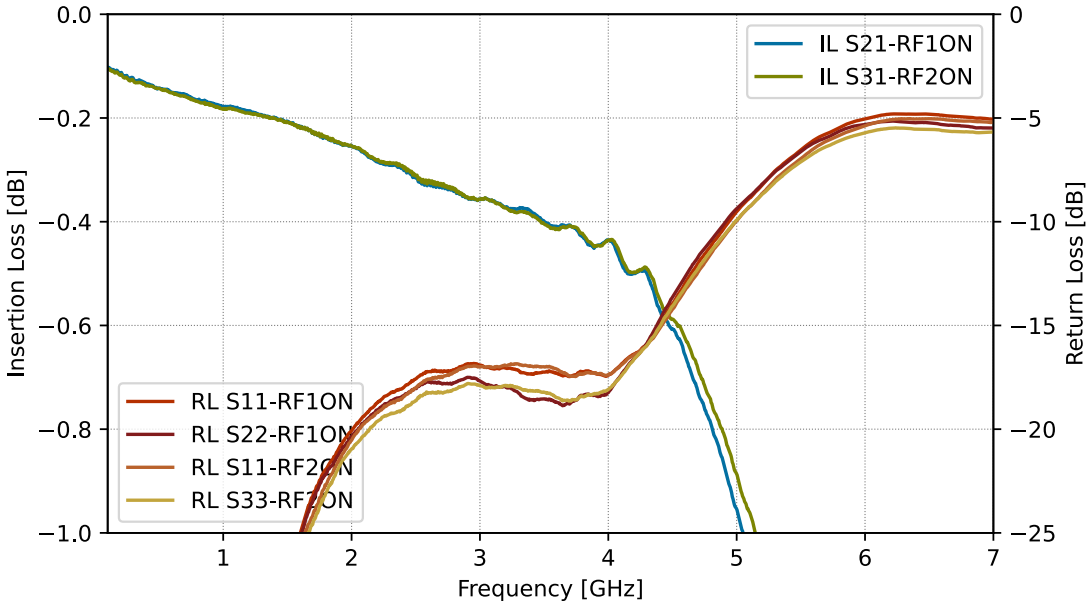
Reference	Part number / Value	Description	Notes
TL_C	2.2mm	CPW length	Edge of SW to edge of capacitor
C_C	0603N0R3BW251	Ceramic capacitor	0.3pF, 250V, ± 0.1pF
TL_1	0.3mm	CPW length	Edge of SW to edge of capacitor
C_1	0603N0R1BW251	Ceramic capacitor	0.1pF, 250V, ± 0.1pF
TL_2	0.3mm	CPW length	Edge of SW to edge of capacitor
C_2	0603N0R1BW251	Ceramic capacitor	0.1pF, 250V, ± 0.1pF
C_{VDD}	10nF	Capacitor	GRM155R71H103KA88
C_{VCP}	0.1μF	Capacitor	GRM155R61E104KA87D

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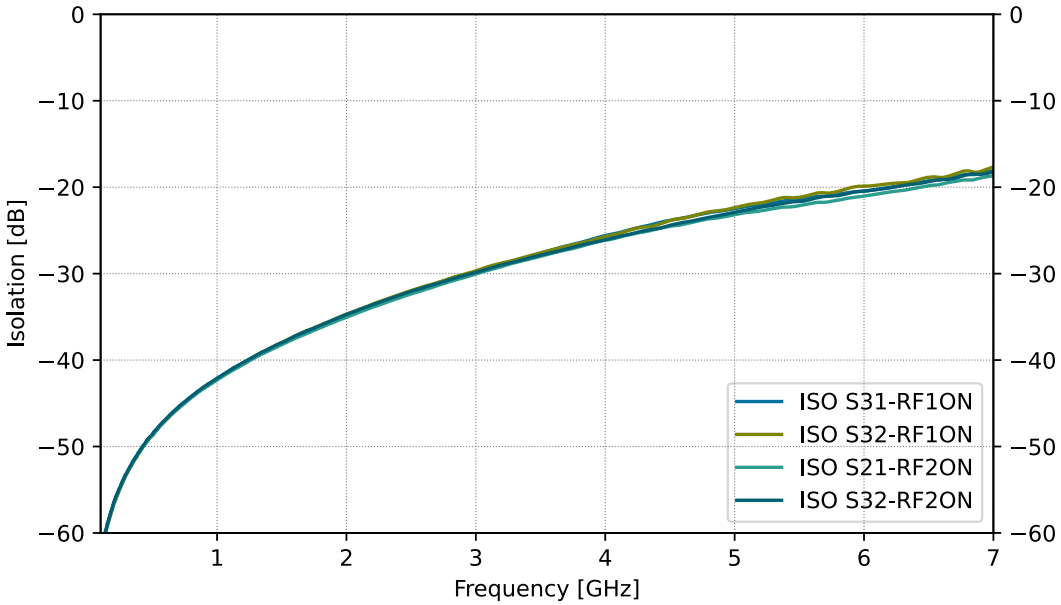
Typical characteristics

Performance upto 4.5 GHz, unmatched

The measurements presented were obtained from the TS8022L EVB with CPW transmission line losses de-embedded from the data. The device operates without requiring matching components for frequencies up to 4.5 GHz. For operation above 4.5 GHz, performance can be enhanced by implementing matching networks at the ports. The provided matching example demonstrates excellent performance up to 6.0 GHz.

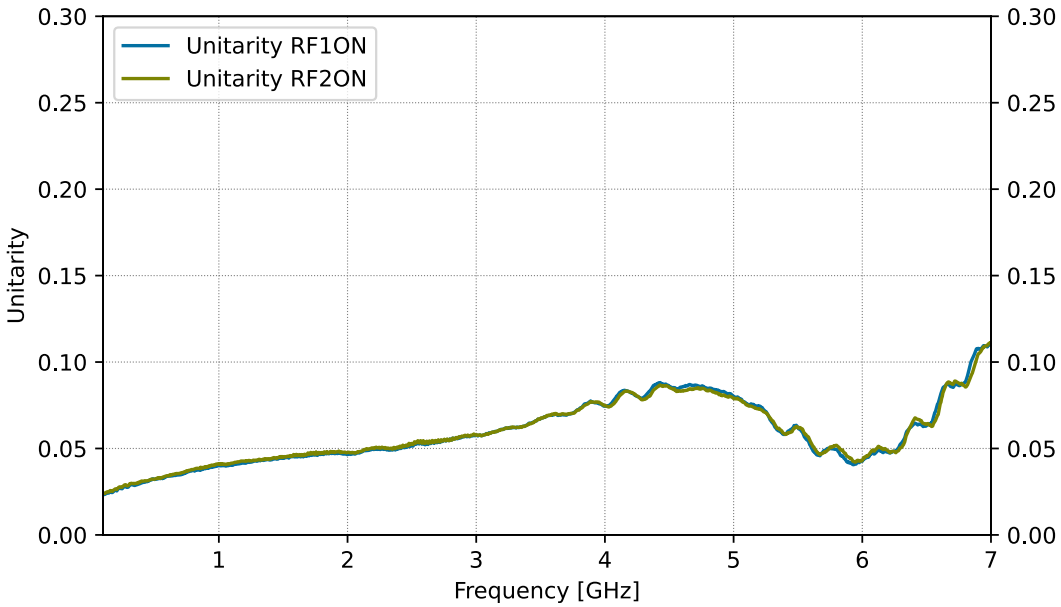


Insertion loss and Return loss, RFC – RFx.

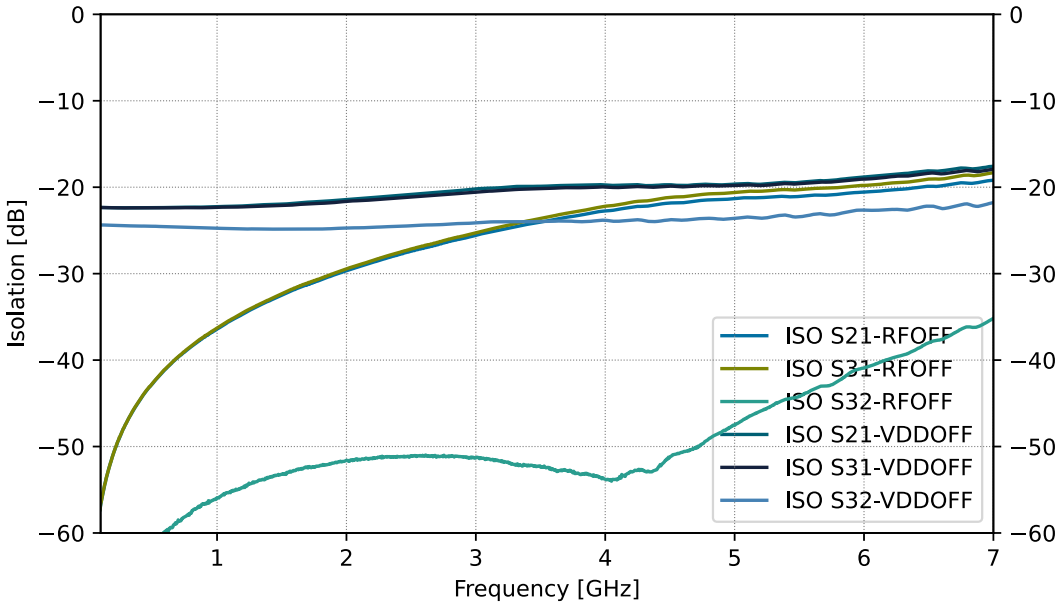


Isolation between RFC to non-active RFx and active RFx to non-active RFx.

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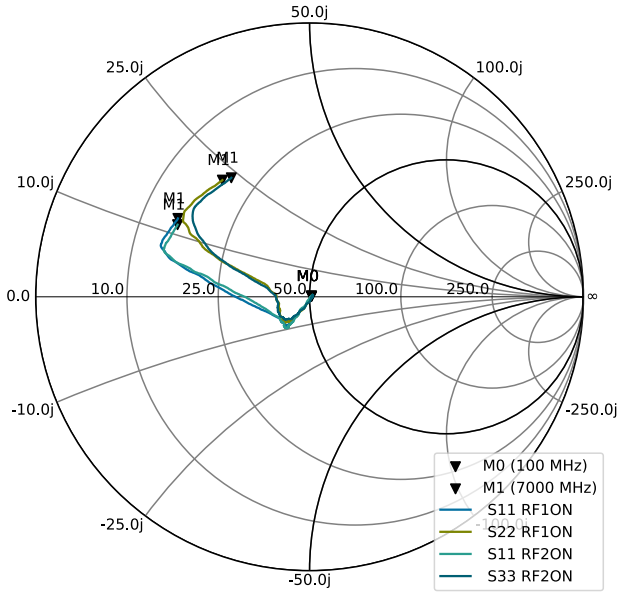


Power absorption of the switch $1 - |S_{11}|^2 - |S_{21}|^2 - |S_{31}|^2$, RFC – RFx.

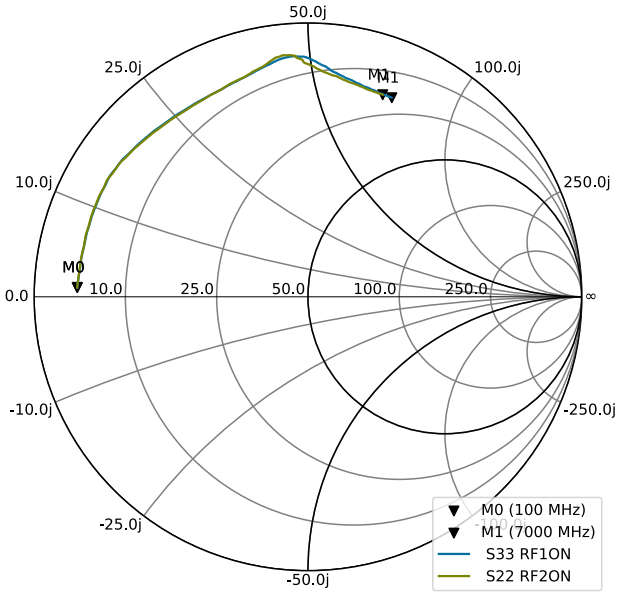


Isolation between RFC to non-active RFx and non-active RFx to non-active RFx at ISO state and V_{DD} off state.

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RFC and RFx matching at ON state.

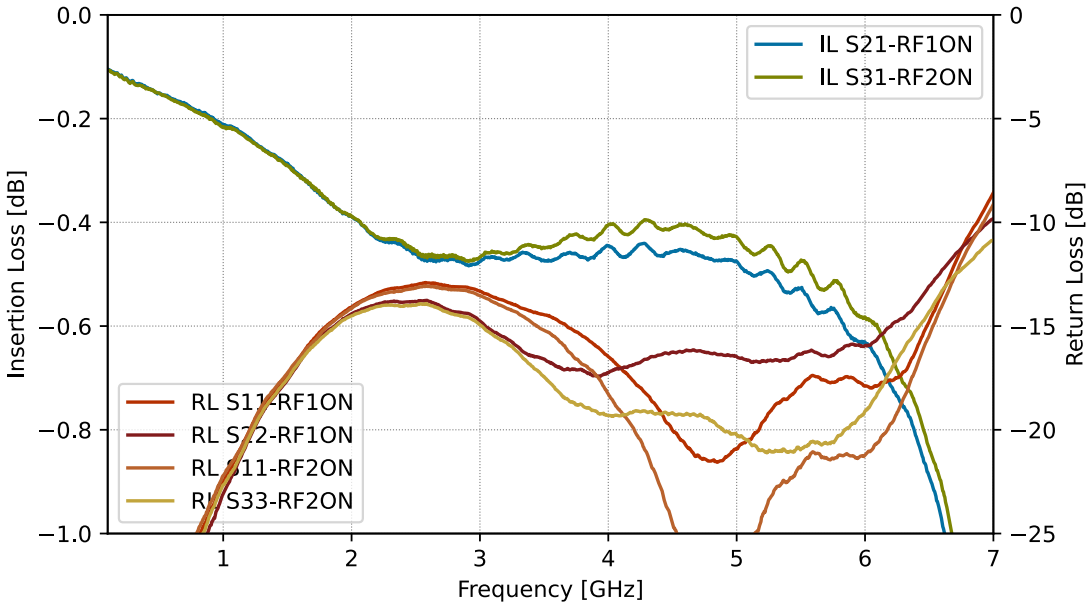


Non-active RFx port impedance. Low frequency starts from closed and circulates towards open at higher frequencies.

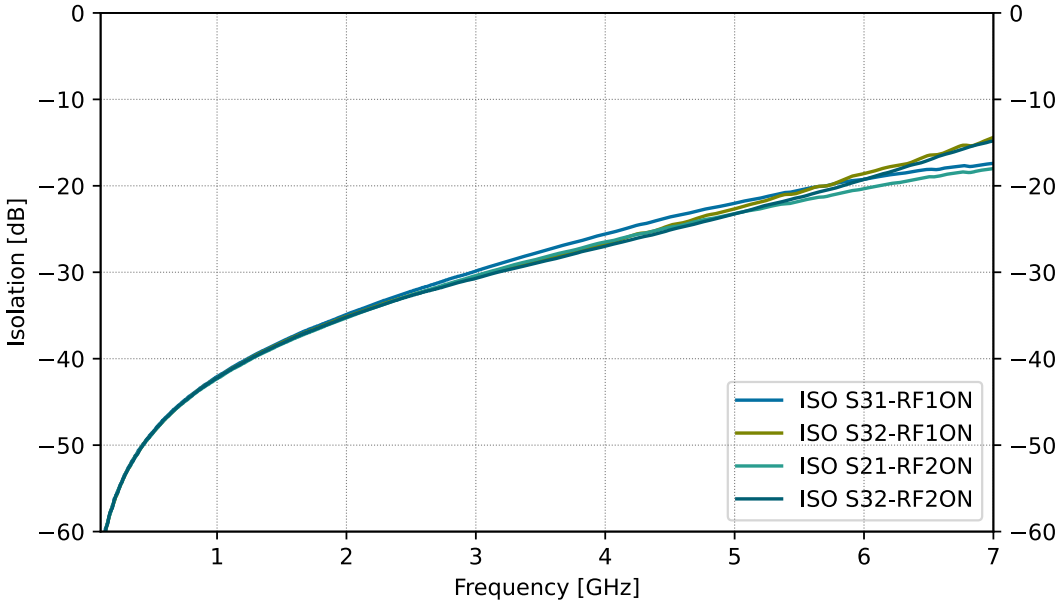
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Performance upto 6000 MHz, matching applied to EVB

The measurements presented were obtained from the TS8022L EVB with matching components implemented. CPW transmission line losses have been de-embedded from the data; however, matching component losses remain included. This example matching configuration extends the corner frequency to 6.0 GHz. For narrower band applications, such as 4.0–5.0 GHz operation, the matching network should be optimized to position the corner frequency closer to 5.0 GHz, which will simultaneously improve low-frequency return loss performance.

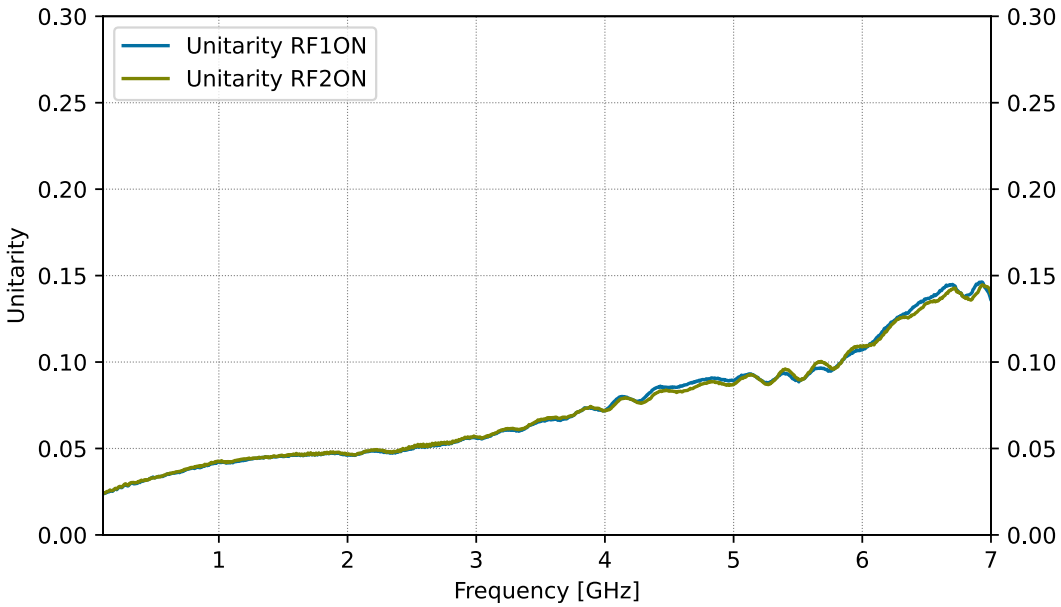


Insertion loss and Return loss, RFC – RFx.

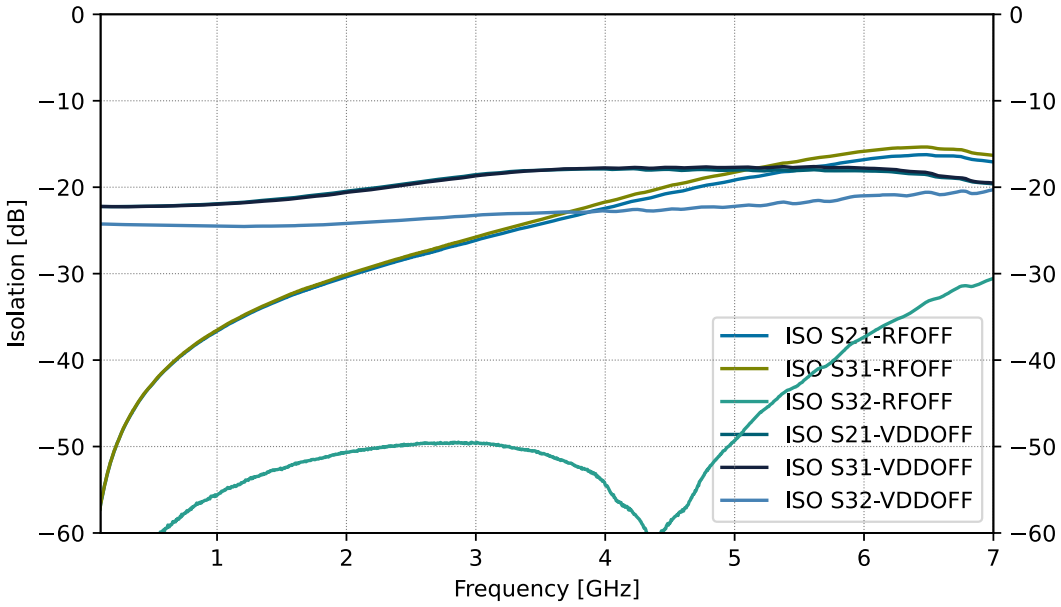


Isolation between RFC to non-active RFx and active RFx to non-active RFx.

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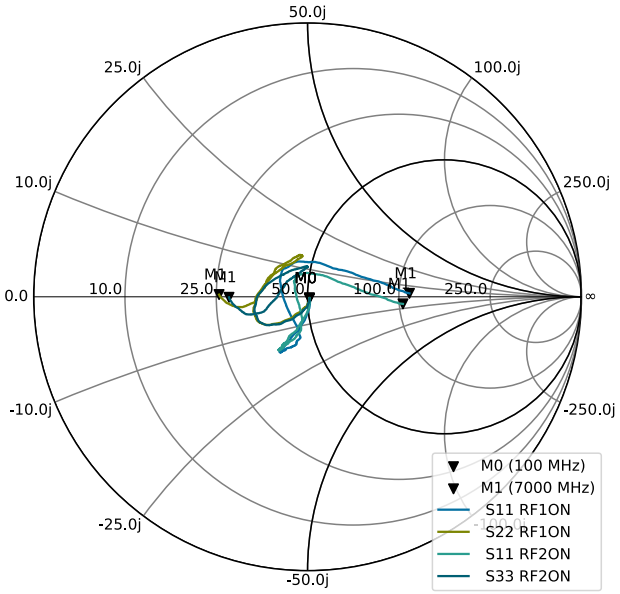


Power absorption of the switch $1 - |S_{11}|^2 - |S_{21}|^2 - |S_{31}|^2$, RFC − RFx.

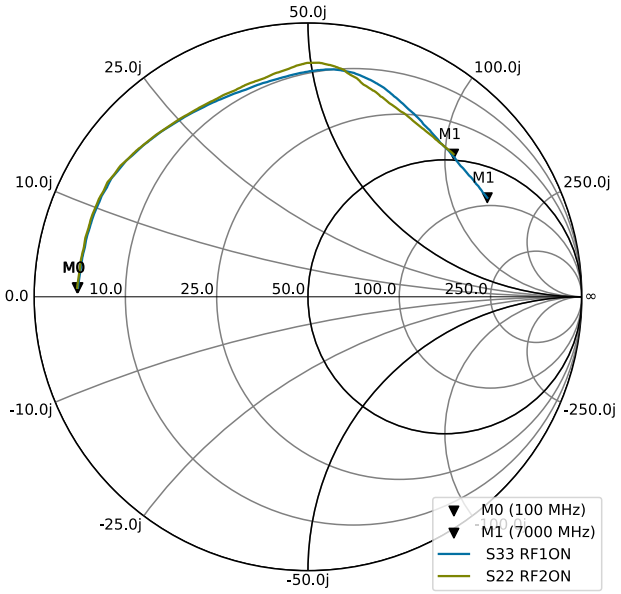


Isolation between RFC to non-active RFx and non-active RFx to non-active RFx at ISO state and V_{DD} off state.

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RFC and RFx matching at ON state.

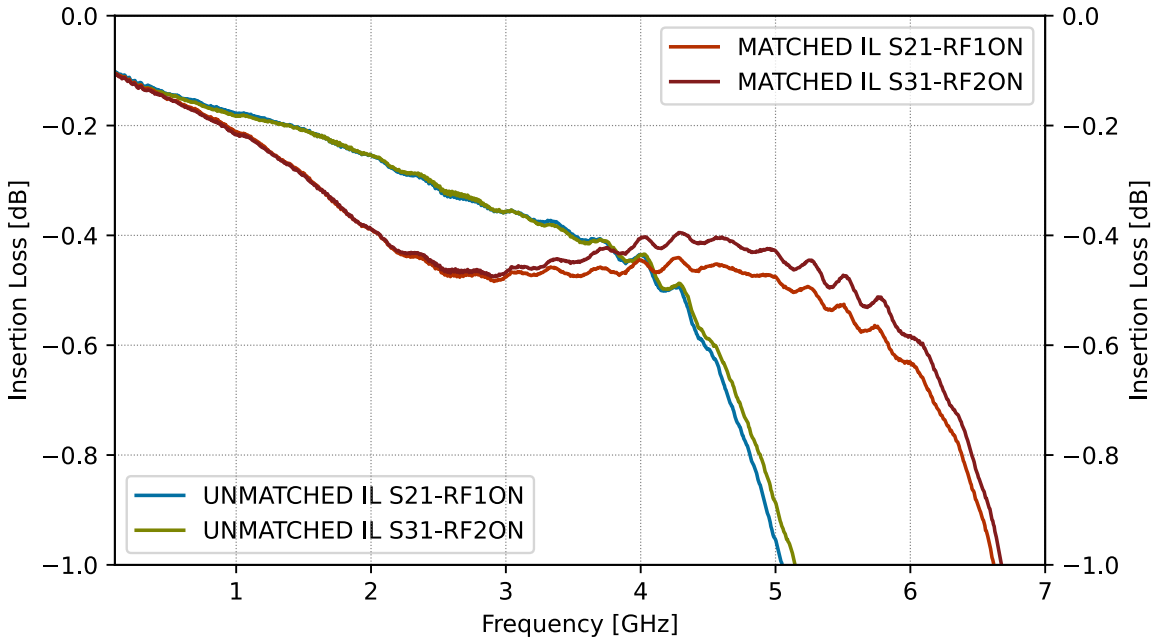


Non-active RFx port impedance. Low frequency starts from closed and circulates towards open at higher frequencies.

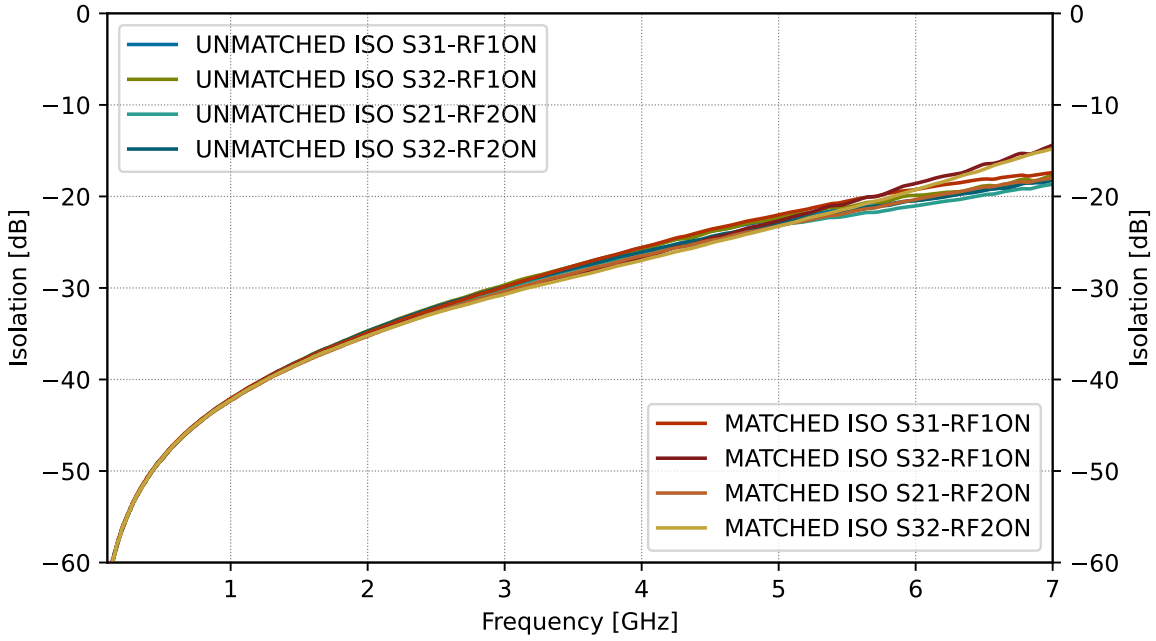
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Comparison plots of matched and unmatched switch.

The following figures present Insertion Loss and Isolation comparison plots for matched and unmatched switch configurations. The matching network extends the usable frequency response up to 6.0 GHz while maintaining isolation performance. For applications operating above 4.0 GHz, implementing the matching network is recommended to optimize performance in this frequency range.



Insertion loss comparison of matched to 6.0 GHz and unmatched switch.

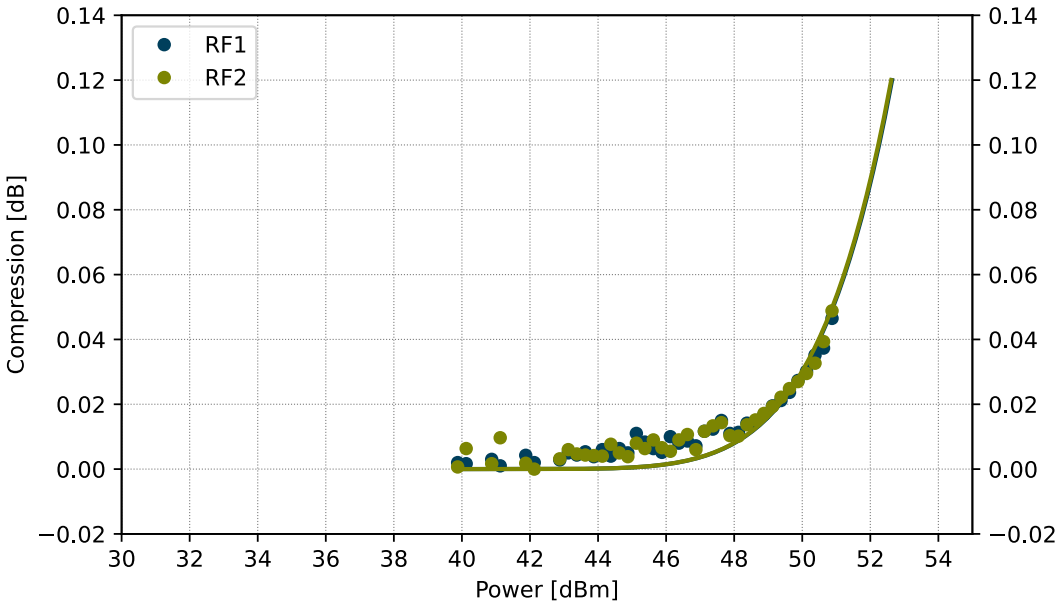


Isolation comparison of matched to 6.0 GHz and unmatched switch.

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Compression measurement

In TagoreTech RF switches, compression is primarily attributed to thermal effects resulting from increased ohmic losses within the device. TS8022L switch exhibits no signal clipping at the 0.1 dB compression point. All measurements were conducted at ambient temperature $T_A = +25°C$. The presented data represents the average of three device samples. Measured data points are indicated by dots (•), while modeled predictions and extrapolations are shown as dashed lines (–).



0.1 dB Compression point measurement, out of 3 parts, results averaged.

Power De-rating

TS8022L has power handling de-rating below 10 MHz. Power de-rating table has been defined for 50 ohm environment.

Table 13: Power De-Rating table

Start f	**Stop** f	**Max Power**	**Unit**
1 MHz	2 MHz	40	dBm
2 MHz	5 MHz	43	dBm
5 MHz	10 MHz	45	dBm
10 MHz	100 MHz	46	dBm
100 MHz	f_{max}	47	dBm

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Device Package information

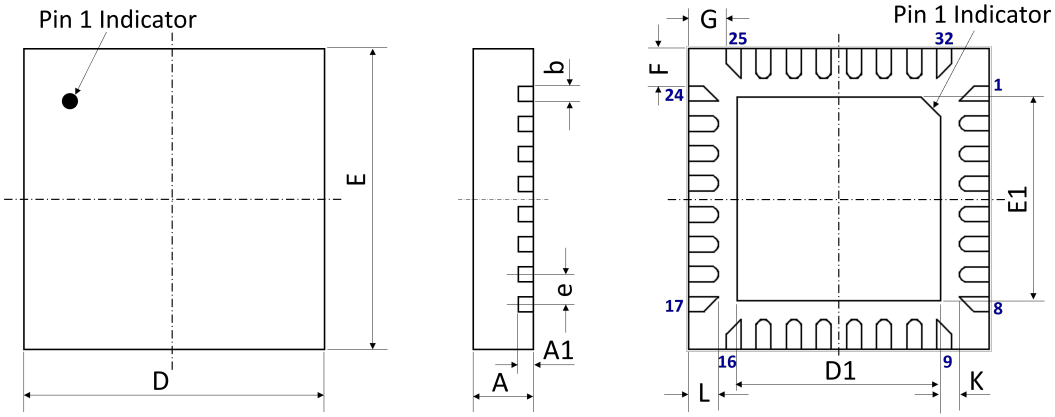
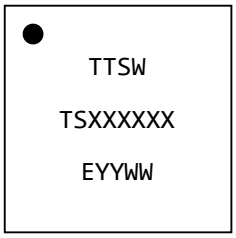


Figure 8: 32-pin QFN 4.0 x 4.0 x 0.85 mm^3 package drawing.

Please refer to application notes TN-001 and TN-002 at TagoreTech web page for PCB and soldering guidelines.

Table 14: Device Package Dimensions

Dimension	Value [mm]	Tolerance [mm]	Dimension	Value [mm]	Tolerance [mm]
A	0.80	±0.05	E	4.00 BSC	±0.05
A1	0.203	±0.02	E1	2.70	±0.05
b	0.20	+0.05/-0.07	F	0.50	±0.05
D	4.00 BSC	±0.05	G	0.50	±0.05
D1	2.70	±0.05	L	0.40	±0.05
e	0.40 BSC	±0.05	K	0.25	±0.05



●	Pin 1 indicator
TTSW	TagoreTech SWitch
TSXXXXXX	Part number (8 digits max)
E	Fixed letter before date code
YY	Last two digits of assembly year
WW	Assembly work week

Figure 9: Part marking specification.

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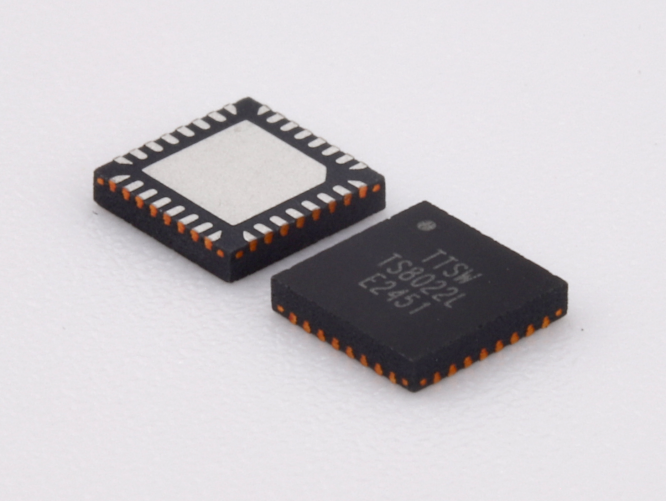


Figure 10: TS8022L photo, top and bottom side.

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PCB Land Design

Notes:

- 4-layer PCB is recommended.
- Via diameter is recommended to be 0.3mm to prevent solder wicking inside the vias.
- Thermal vias shall only be placed on the center pad.
- The maximum via number for the center pad is 11(X)×11(Y)=121.

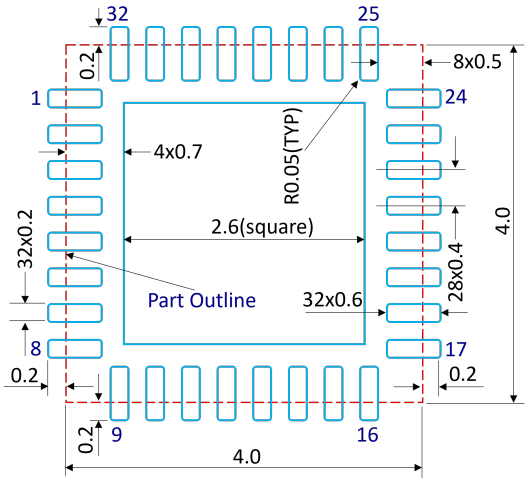


Figure 11: PCB land pattern, dimensions in [mm].

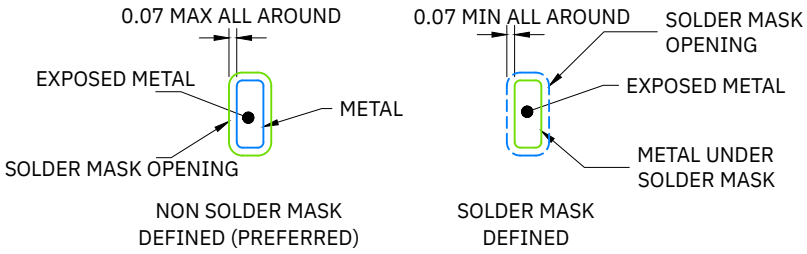


Figure 12: Solder mask opening, dimensions in [mm].

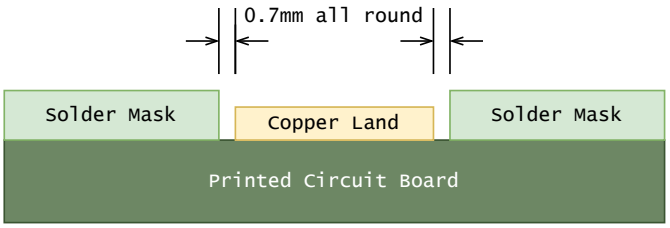


Figure 13: Preferred solder mask opening, side view, dimensions in [mm].

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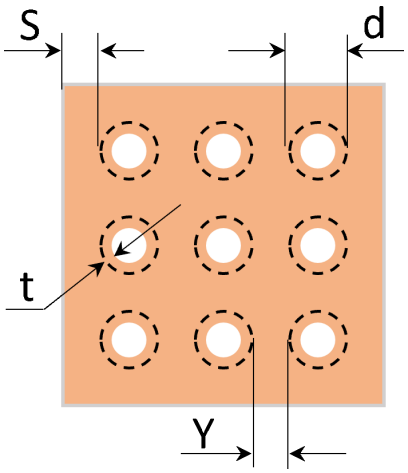


Figure 14: Thermal Via Pattern, Recommended Values: S≥0.15mm; Y≥0.20mm; d=0.2mm; Plating Thickness t=25μm or 50μm.

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PCB Stencil Design

Notes:

- Laser-cut, stainless steel stencil is recommended with electro-polished trapezoidal walls to improve the paste release.
- Stencil thickness is recommended to be 125μm.

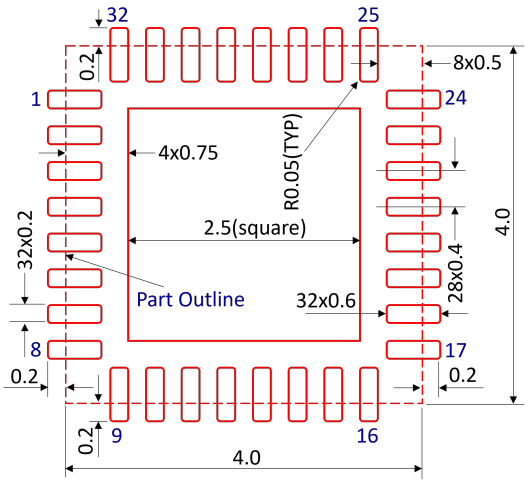


Figure 15: Stencil Openings, dimensions in [mm].

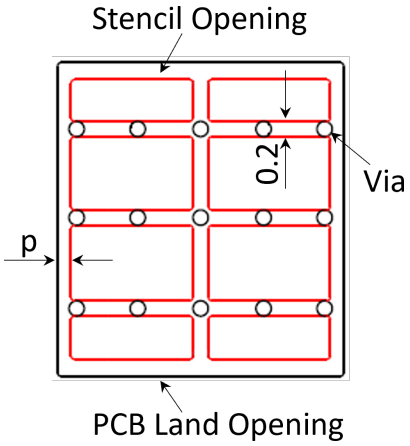
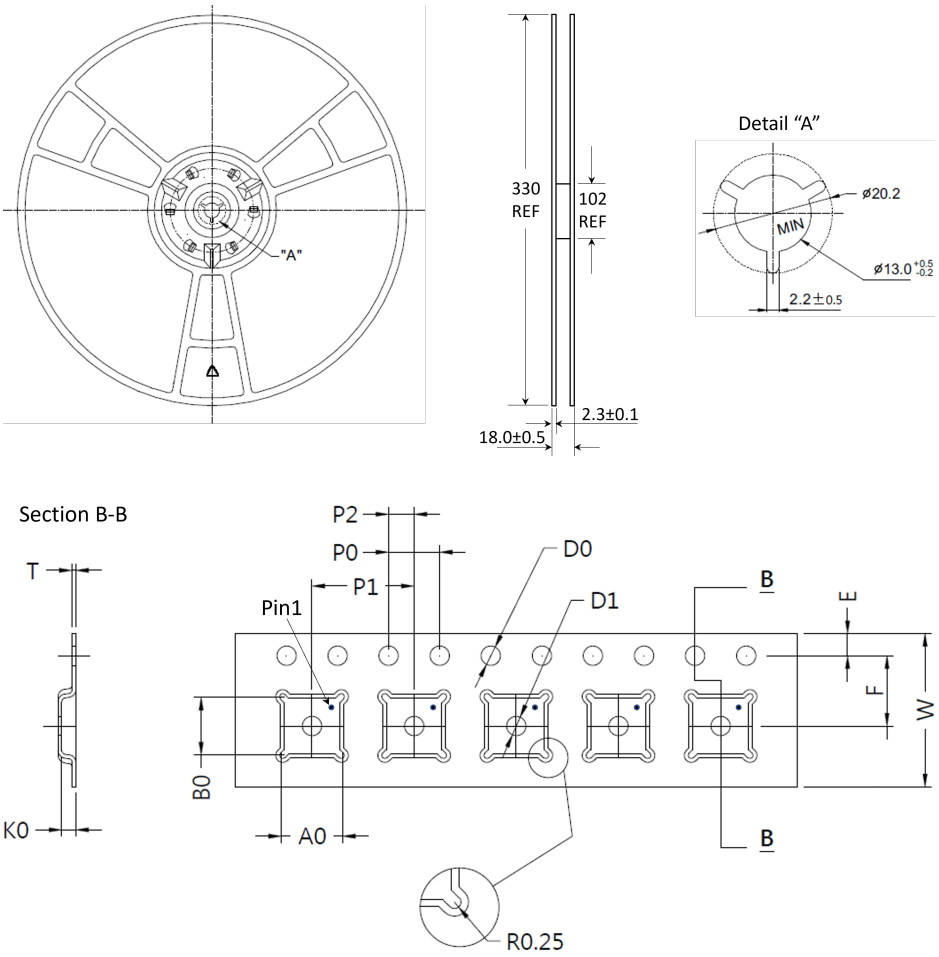


Figure 16: Stencil Openings Shall not Cover Via Areas If Possible, dimensions in [mm].

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Tape and Reel Information



A0[mm]	B0[mm]	D0[mm]	D1[mm]	E[mm]	F[mm]	K0[mm]	P0[mm]	P1[mm]	P2[mm]	T[mm]	W[mm]
4.35	4.35	1.50	1.50	1.75	5.50	1.10	4.00	8.00	2.00	0.30	12.00

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Glossary

IL	Insertion loss
ISO	Isolation
RL	Return loss
VSWR	Voltage Stading Wave Ratio
RFC	RF Common port, sometimes referred as ANT
RFx	RF Port number x
Unitarity	Describes power absorption of the component, $1 - \|S_{11}\|^2 - \|S_{21}\|^2 - \|S_{31}\|^2$

Changelog

Table 15: Changelog

Date	Revision	Notes
01/02/2026	3.0	New release with updated information, frequency range extended from 1 MHz to 6.0 GHz
01/26/2026	3.01	Mistake corrected in matched schematics regarding NC pins.
04/16/2026	3.02	RoHS10 and Control Voltage can be maximum Vdd.
05/18/2026	3.03	Switching time characterization frequency updated and added compression graph.

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